



First Principle Investigation on Thermoelectric Properties of TMDC: Beyond Rigid Band Model

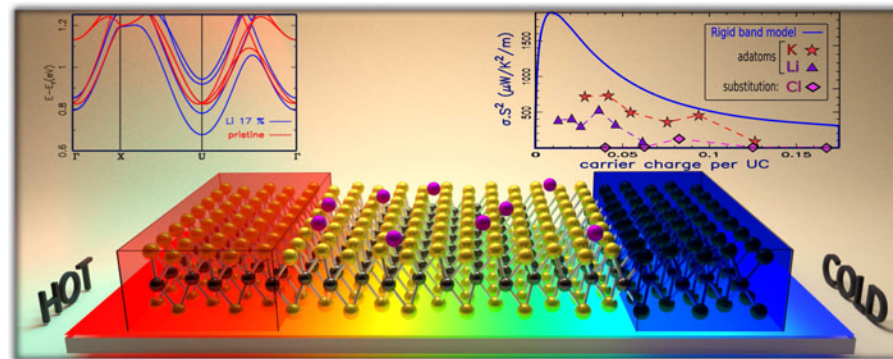
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Outlines

- The Basics of the Seebeck Effect
- The structure of TMDCs and the Doping Issue
- Primary Results with Rigid Band Shift Model
- Doped TMDC (*ab-initio*)
- Power Factor using Realistic Doping (w disorder)
- Concluding Remarks



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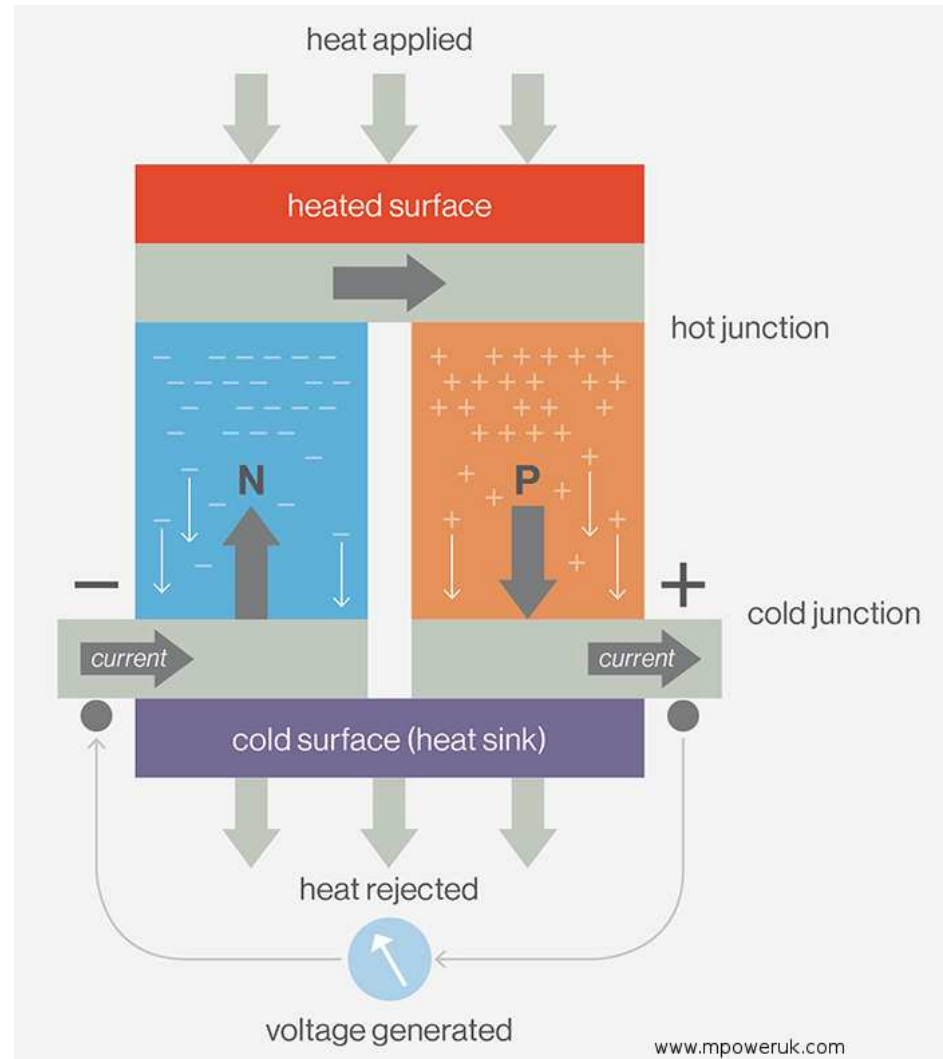
The Seebeck Effect

Thomas Johann Seebeck

(1770-1831)

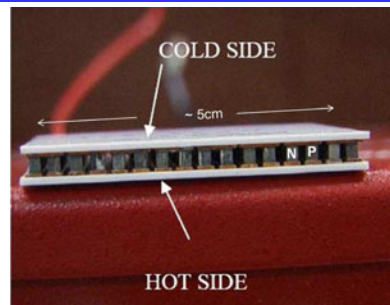


Electromotive force caused by temperature gradient (input) across two dissimilar conducting metals, which form a closed loop.



Seebeck Coefficient:

$$S = \frac{\Delta V}{\Delta T}$$



$$\begin{cases} \text{N type} & \Rightarrow S < 0 \\ \text{P type} & \Rightarrow S > 0 \end{cases}$$

Device Efficiency

The ability of a given material to efficiently produce thermoelectric power is related to the figure of merit:

$$ZT = \frac{\sigma \cdot S^2 \cdot T}{\kappa}$$

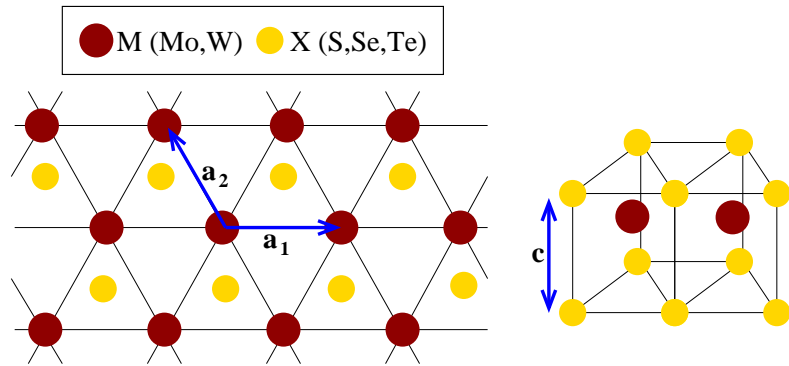
$\sigma \cdot S^2$: Power Factor (PF)

κ : Thermal Conductivity

⇒ A good TE material has a large PF and a small κ

- 2D materials (like TMDC) are expected to have a low thermal conductance.
- It is possible to reduce κ by phonon engineering.
- To obtain the largest Power Factor (PF), we need a large σ and a large S .
 - Metal have large σ and poor S .
 - Semiconductor have very poor σ and large S .
- One way to obtain a large PF is to use doped semiconductor.
- We have investigated two technics: substitution and adsorption doping.

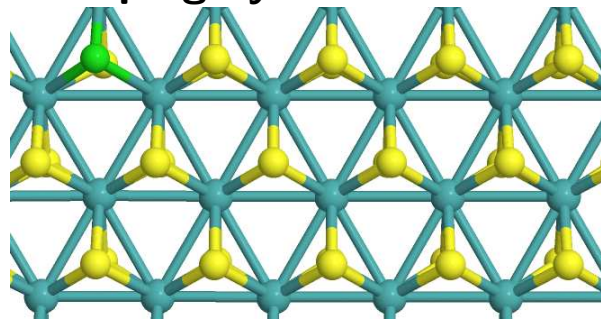
TMDC's Structure



- TMDC (MX_2) \Rightarrow honeycomb structure.
- Made up of layered X-M-X sheets.
- Two hexagonal sheets of X atoms and an intermediate hexagonal sheet of M atoms.
- Monolayer TMDC are semiconductor with direct band-gap.

Doping Issue

Doping by Substitution:



Hole doping
Electron doping

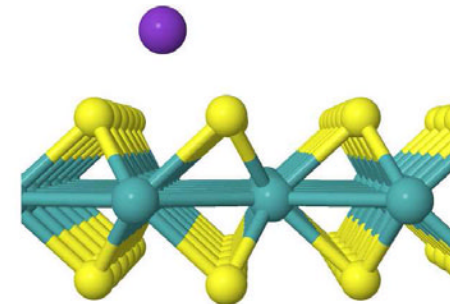
15 P phosphorus 30.97	16 S sulfur 32.06	17 Cl Chlorine 35.45
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41 Nb Niobium 92.91	42 Mo molybdenum 95.96
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73 Ta Tantalum 180.95	75 Re Rhenium 186.207
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Doping by Adsorption:

3 Li lithium 6.94	11 Na Sodium 22.99	19 K potassium 39.098	37 Rb Rubidium 85.47
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Alkali metals come as e^- donors

Outstanding Experimental achievement:

N-doping of MoS_2 by surface charge transfer using K.

(Fang *et al.* Nano Letters 2013, 13, 1991-1995)

A Few Words About Theory

⇒ The PF is obtained using *ab-initio* calculations and Green's function technics (NEGF) on the basis of Landauer-Büttiker formalism

Boltzmann

- Semi-classical theory
- Scattering mechanisms described by:
Relaxation Time (τ)

It gathers all scattering mechanisms:
(defects, $e^- - e^-$, $e^- - \text{phonons}$...)

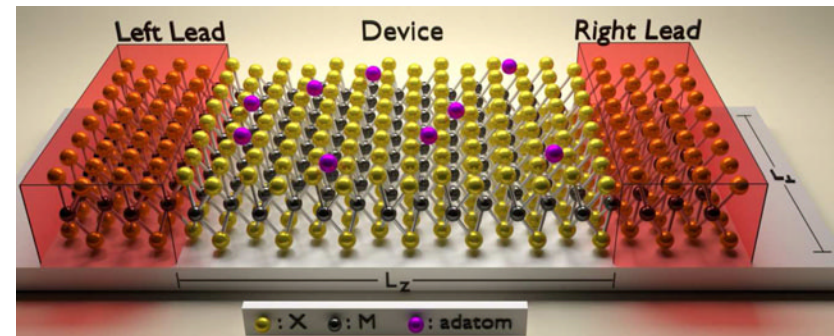
NEGF

- Full *ab initio* theory
- Based on localized basis set (SIESTA)
- Scattering mechanisms have to be defined

Insight on disorder scattering

S and G are computed using the Transmission:

$$G = -\frac{2e^2}{\hbar} \int_{-\infty}^{+\infty} T(E) \left(\frac{\partial f}{\partial E} \right) dE,$$
$$S = -\frac{1}{k_B T} \frac{\int_{-\infty}^{+\infty} (E - E_F) T(E) \left(\frac{\partial f}{\partial E} \right) dE}{\int_{-\infty}^{+\infty} T(E) \left(\frac{\partial f}{\partial E} \right) dE}.$$



Within this formalism, it is possible to deal with realistic disordering.

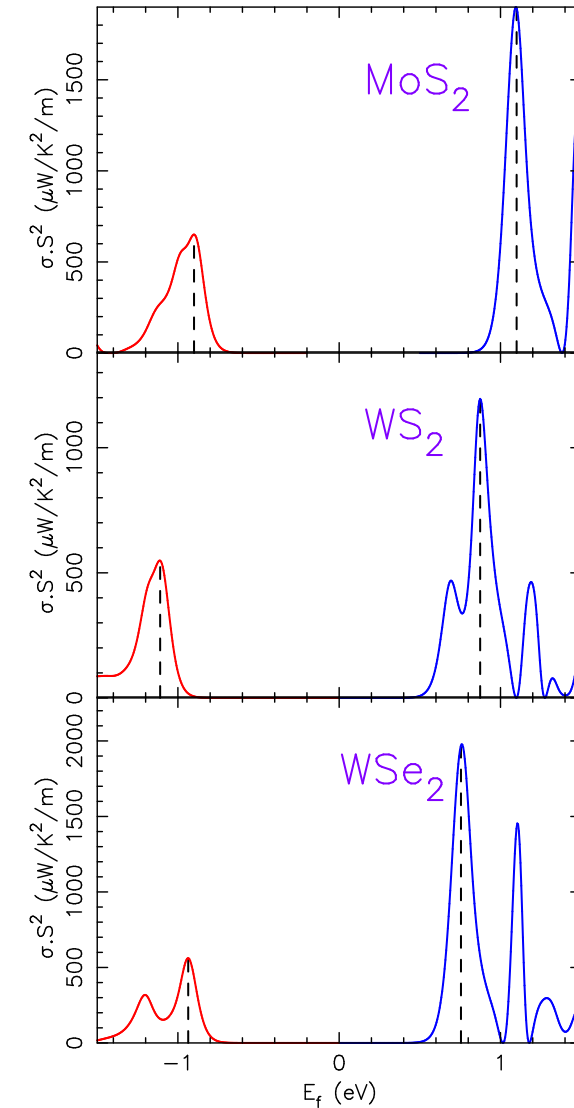
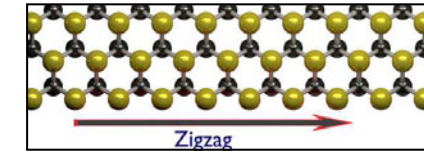
Transport Using Rigid Band Shift

Rigid shift of the fermi-level \Rightarrow Carrier doping by field effect.

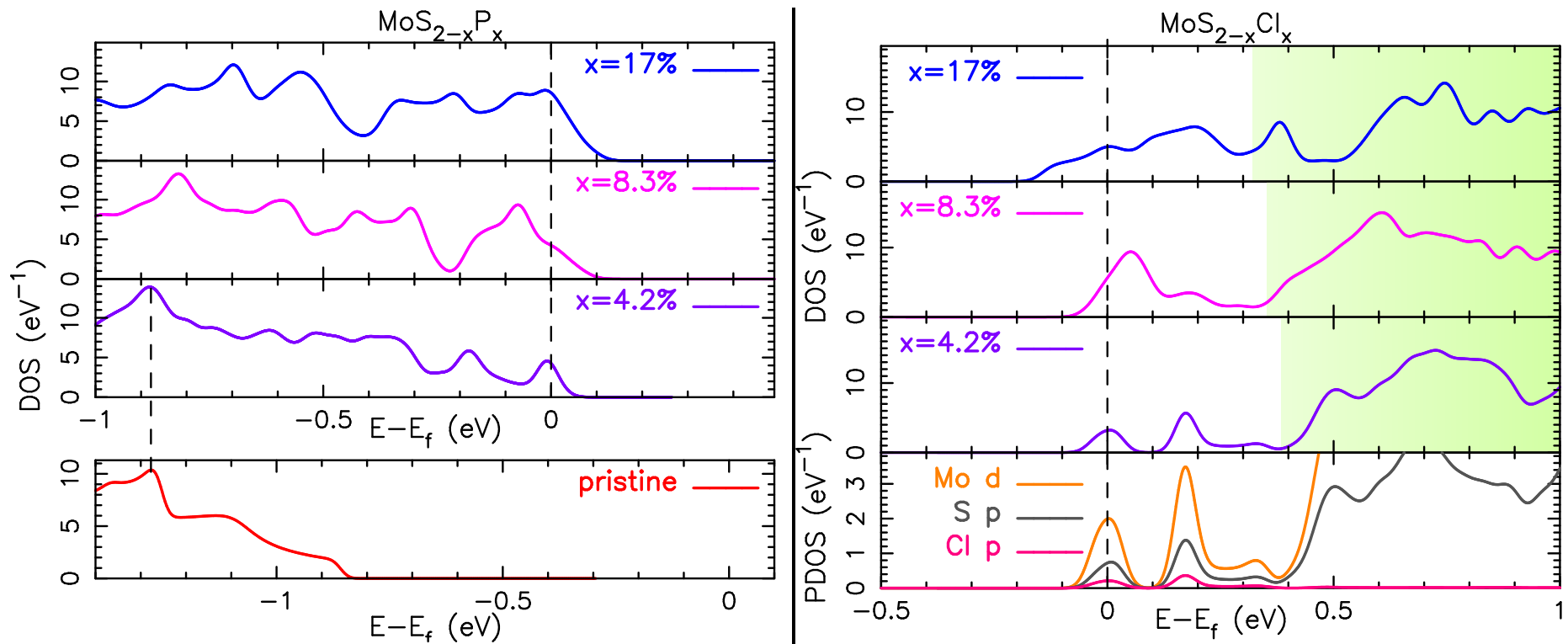
- PF_{\max} linked with 2 opposite trends
 - $\sigma \nearrow$ with $|E_f|$
 - $S \searrow$ with $|E_f|$
- Aim: To access the largest PF with a doping technique.

	$S(\mu\text{V}/\text{K})$	$\sigma(\mu\text{S}/\text{\AA})$	PF ($\mu\text{W}/\text{K}^2/\text{m}$)	carrier charge per UC $\times 100$
MoS ₂	-157.	8.	1888	+1.
MoSe ₂	-87.	20.	1480	+9.
WS ₂	-86.	16.	1193	+6.5
WSe ₂	-173.	7.	1968	+1.5

- Hole doping leads to lower PF.
- Largest PF for MoS₂ and WSe₂ for moderate carrier doping.
- Armchair transport direction leads to similar results.

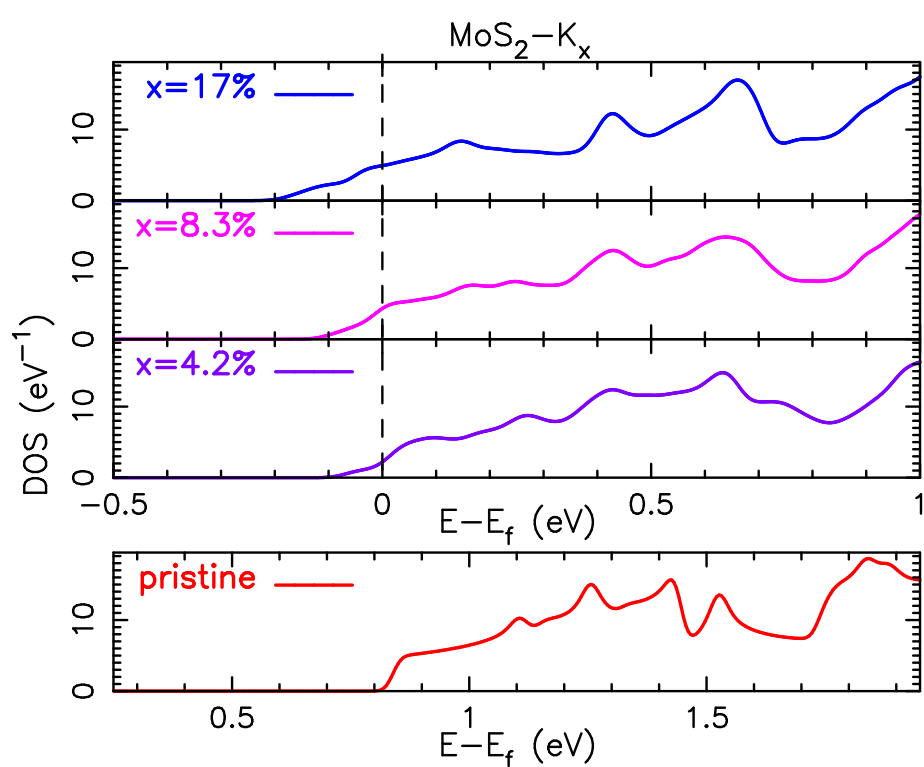


Ab initio Calculations For Substitution Doping

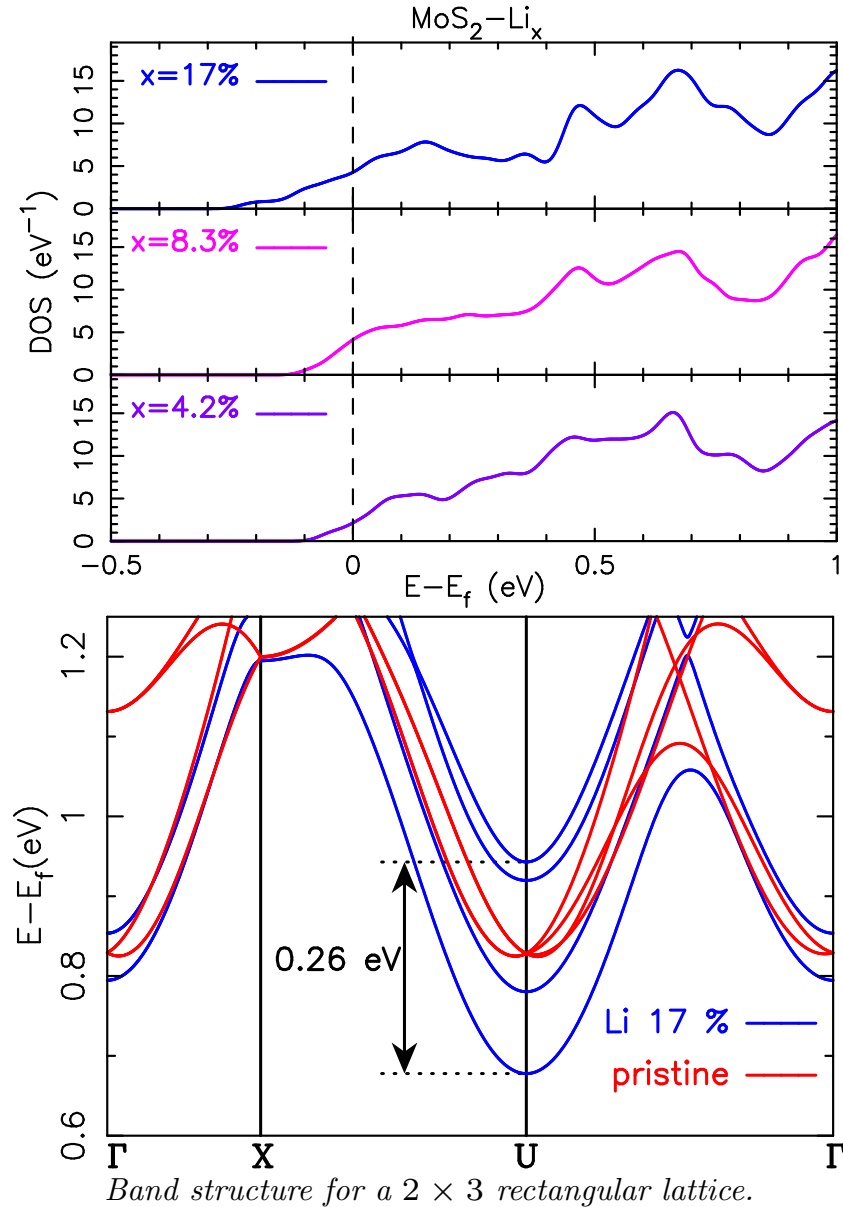


- Substitution doping by P and Cl is leading to donor states at the Fermi level.
- This is also observed with F, Br and Re.
- These states lead to almost flat bands at low doping concentration.

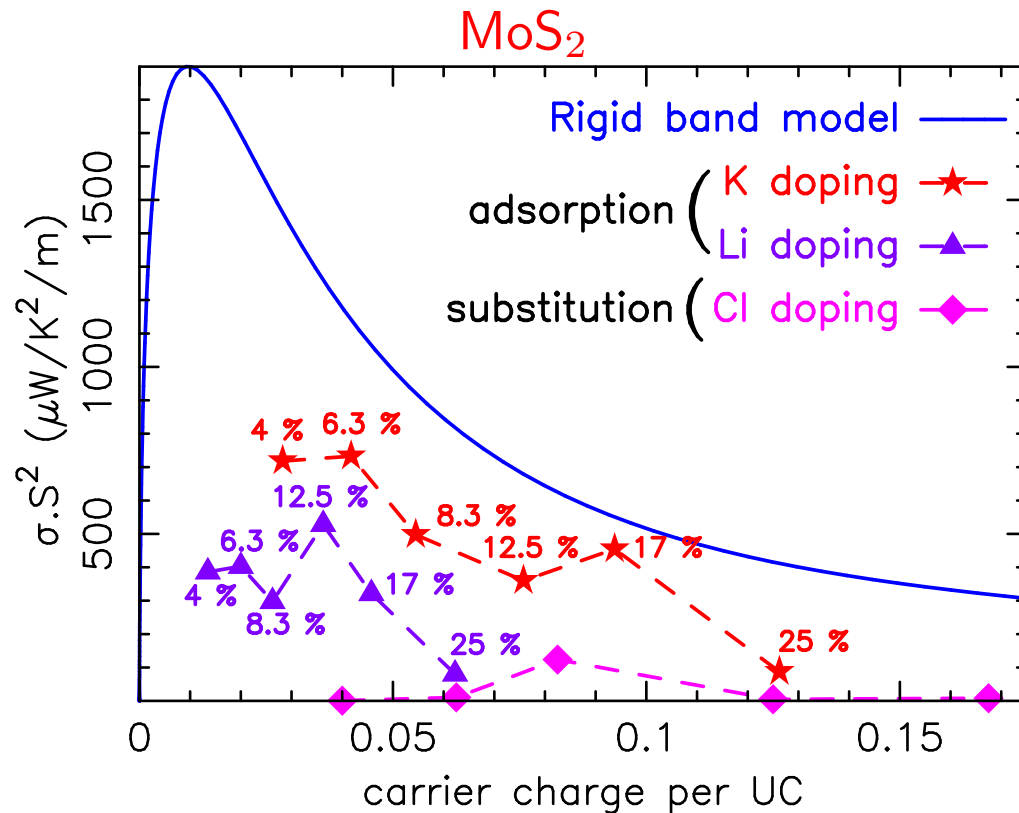
Adsorption Doping



- Alkalies are creating states at much more higher energies than the first conduction band.
- They act almost as perfect donors (band shifting).
- however they affect a bit the dispersion of the bands and remove some degeneracies.



Power Factor Under Real Doping



Chloride

- Very poor PF for Cl
- At low concentration \Rightarrow Poor σ

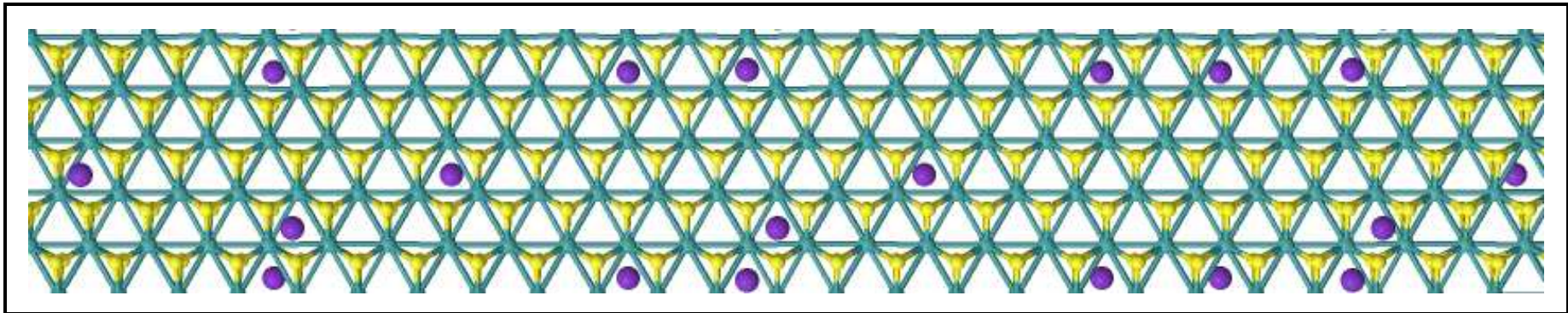
Alkali

- Much closer to the Rigid band model.
- Large atoms (K or Rb) are better candidates than the smaller one (Li or Na).

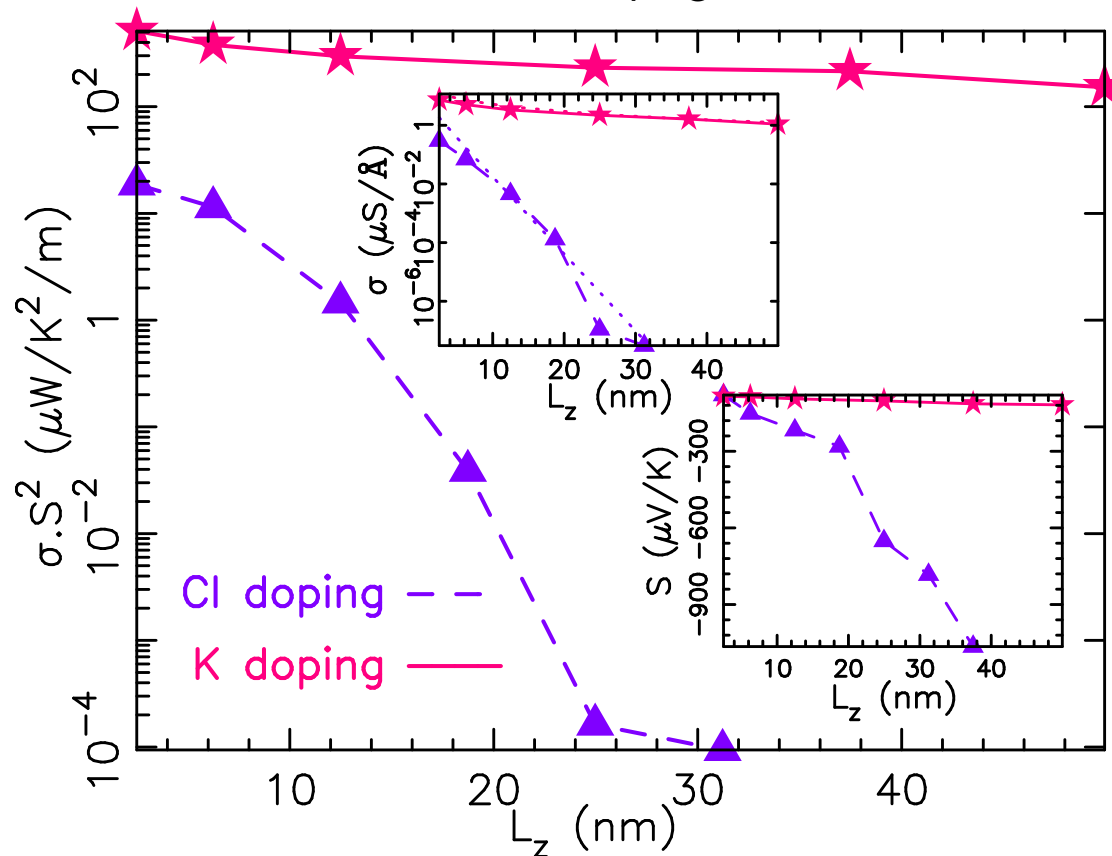
- Lower conductance for Li and Na.
- Lower PF for MoSe₂ and WSe₂
- MoS₂ and WSe₂ are the best candidates

	4.2%	σ ($\mu\text{S}/\text{\AA}$)	S ($\mu\text{V}/\text{K}$)	PF ($\mu\text{W}/\text{K}^2/\text{m}$)
MoS ₂	Na	2.	-105.	200.
	Rb	6.	-113.	728.
MoSe ₂	K	5.	-79.	289.
WSe ₂		4.	-150.	929.

Scattering by Disorders



12.5% doping



Chloride

- The conductivity decay is not compensated by the Seebeck increase with the length.

- Anderson Localization

Potassium

- The PF variation is only one order of magnitude for a 50 nm length system.

Coherence length (L_c)

$$\rho(L) \propto e^{2L/L_c} - 1$$

- Cl \Rightarrow 3.5 nm

- K \Rightarrow 1.5 μm

Concluding Remarks

- Rigid band model should be handled with care
- Cl and P lead to donor states at the FL
- Chloride leads to an Anderson localization
- Alkalies act almost as perfect e^- donors

Thanks for your attention!